Supporting Information for

Controllable Growth of Transition Metal Dichalcogenides Multilayer Flakes with Kirigami Structures

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Fig. S1 The T-t curves of the reaction process measured by armored thermometers. When the central temperature reaches 850 °C, Se vapor overflows (217 °C), resulting in a Se-rich conditions during the whole growth process.



Fig. S2 Edge size variations and the corresponding histograms of $MoSe_2$ multilayer flakes at different deposition temperature in Fig. 1e–h.



Fig. S3 (a–c, d–f, g–i) The corresponding XPS spectra of MoSe₂ multilayer flakes at different deposition temperature in Fig. 1e, 1g, 1h.



Fig. S4 The corresponding 3D AFM images of Kirigami-structured MoSe₂ multilayer flakes in Fig. 2e, 4c and 4f.



Fig. S5 SEM images of the Kirigami-structured WSe₂ multilayer flakes with different contrast.